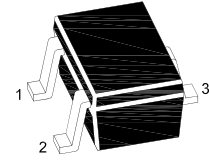
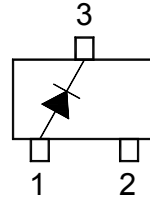


1SS397W

Silicon Epitaxial Planar Diodes

High Voltage Switching Diode

For high voltage and high speed switching applications



Marking Code: **HV**
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	420	V
Reverse Voltage	V_R	400	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current ($t_p = 10\text{ ms}$)	I_{FSM}	2	A
Power Dissipation	P_D	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	1.3	V
Reverse Current at $V_R = 300\text{ V}$ at $V_R = 400\text{ V}$	I_R I_R	- -	0.1 1	μA
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	-	5	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$	t_{rr}	0.5	-	μs

